

# Micro-spectrometer

C12666MA



## Finger-tip size, ultra-compact spectrometer head integrating MEMS and image sensor technologies

The C12666MA is an ultra-compact (Finger-tip size) spectrometer head developed based on our MEMS and image sensor technologies. The adoption of a newly designed optical system has achieved a remarkably small size, less than half the volume of the previous mini-spectrometer MS series (C10988MA-01). In addition, the employment of hermetic packaging has improved humidity resistance.

This product is suitable for integration into a variety of devices, such as integration into printers and hand-held color monitoring devices that require color management. It is also suitable for applications that collaborate with portable devices, such as smartphones and tablets.

### Features

- **Finger-tip size: 20.1 × 12.5 × 10.1 mm**
- **Weight: 5 g**
- **Spectral response range: 340 to 780 nm**
- **Spectral resolution: 15 nm max.**
- **Hermetic package: High reliability against humidity**
- **Installation into mobile measurement equipment**
- **Wavelength conversion factor\*1 is listed on final inspection sheet**

\*1: A conversion factor for converting the image sensor pixel number into a wavelength. A calculation factor for converting the A/D converted count into the input light level is not provided.

### Applications

- **Color monitoring for printers and printing machines**
- **Testers for lights and LEDs**
- **Color adjustment of various large size displays**
- **Water quality control monitors and other environment measuring instruments**
- **Measuring instruments that use portable devices such as smartphones and tablets**

### Optical characteristics

Parameter	Value	Unit
Spectral response range	340 to 780	nm
Spectral resolution (FWHM)	15 max.	nm
Wavelength reproducibility*2	-0.5 to +0.5	nm
Wavelength temperature dependence	-0.1 to +0.1	nm/°C
Spectral stray light*3	-25	dB

\*2: Measured under constant light input conditions

\*3: Spectral stray light =  $10 \times \log (Tl/Th)$

Th: count measured when light at a certain wavelength is input

Tl: count measured at a wavelength 40 nm longer or shorter than the input light wavelength

### Electrical characteristics

Parameter	Min.	Typ.	Max.	Unit
Supply voltage	4.75	5	5.25	V
Power consumption	-	30	-	mW
Video rate	0.25	-	200	kHz
Output impedance	-	150 *4	-	$\Omega$

\*4: An increase in the current consumption at the video output terminal also increases the chip temperature and so causes the dark current to rise. To avoid this, connect a buffer amplifier for impedance conversion to the video output terminal so that the current flow is minimized. As the buffer amplifier, use a JFET or CMOS input operational amplifier of optical input impedance.

**Structure**

Parameter	Specification	Unit
Dimensions (W × D × H)	20.1 × 12.5 × 10.1	mm
Weight	5	g
Slit*5 (H × V)	50 × 750	μm
NA*6	0.22	-
Image sensor (H × V)	CMOS linear image sensor with a slit	-
Number of pixels	256	pixels
Pixel size (H × V)	12.5 × 1000	μm

\*5: Entrance slit aperture size  
 \*6: Numeric aperture (solid angle)

**Absolute maximum ratings**

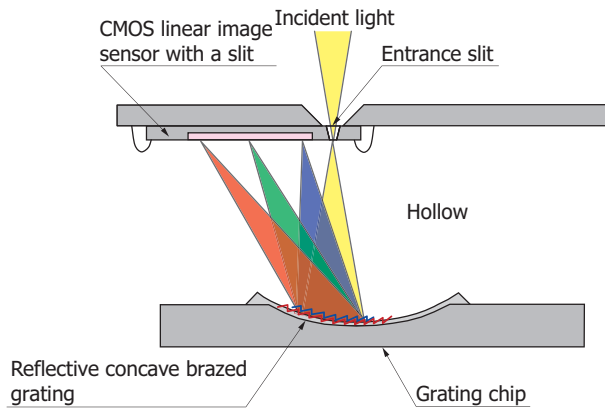
Parameter	Value	Unit
Operating temperature*7	+5 to +50	°C
Storage temperature*7	-20 to +70	°C

\*7: No condensation  
 Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

**Optical component layout**

Besides a CMOS image sensor chip integrated with an optical slit by etching technology, the C12666MA employs a reflective concave brazed grating formed by nanoimprint. In addition, the glass used in the light path of the previous C10988MA-01 is not used in the C12666MA, making it extremely compact.

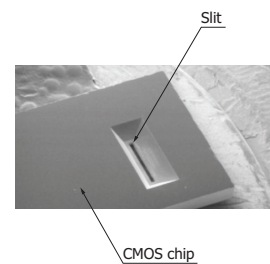
**Structure**



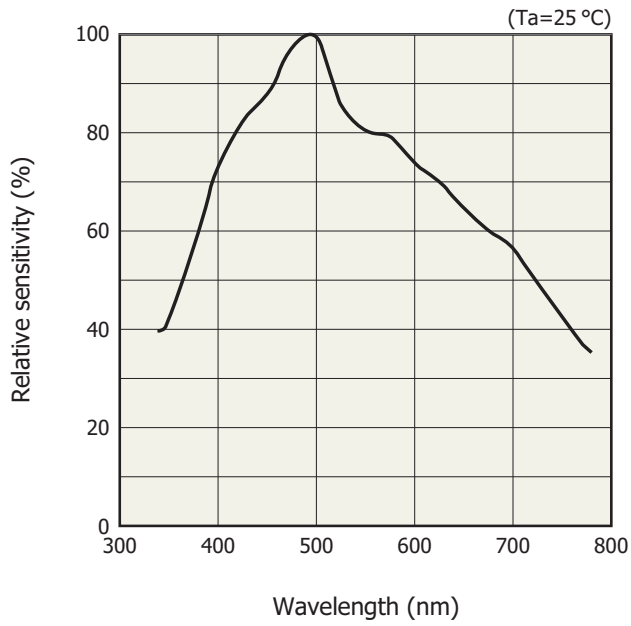
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**CMOS linear image sensor with a slit [Incident light side (back of chip)]**

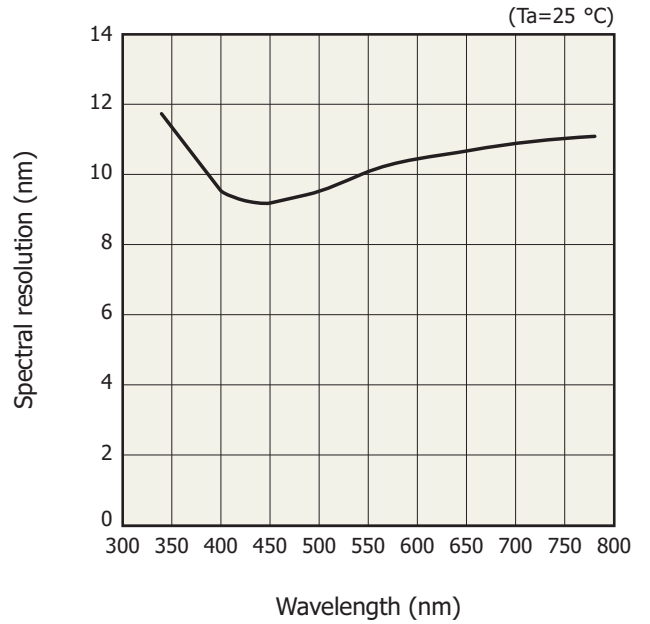


▣ Spectral response (typical example)



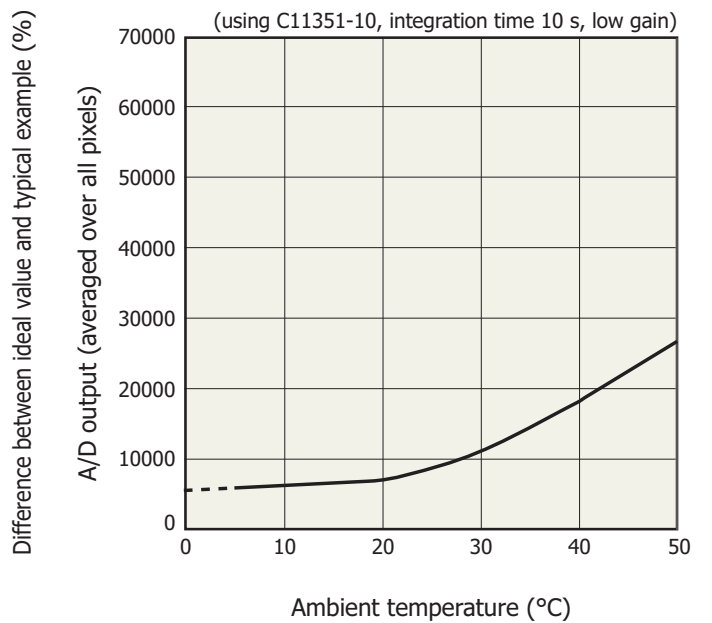
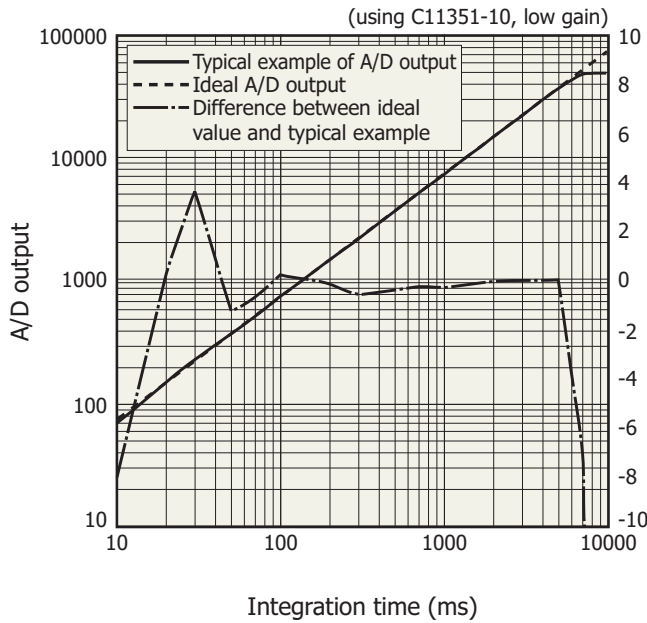
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▣ Spectral resolution vs. wavelength (typical example)



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▣ Linearity (typical example)



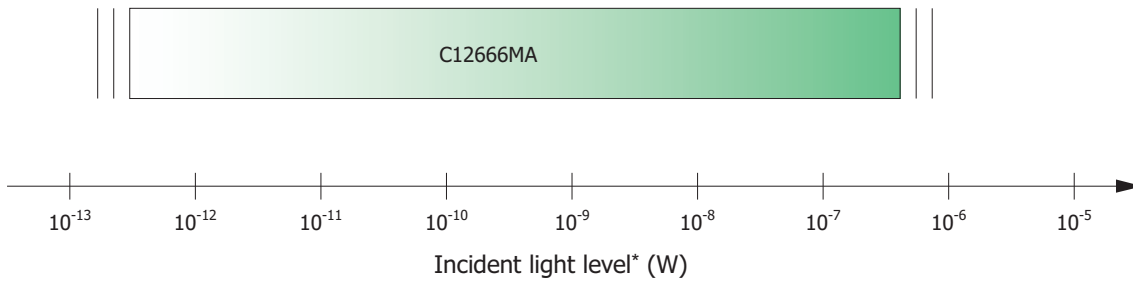
A/D output is the output with dark output is subtracted when light is input. The difference between the ideal value and typical example contains a measurement error. The smaller the A/D output, the larger the measurement error.

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A/D output is the sum of the sensor and circuit offset outputs and the sensor dark output.

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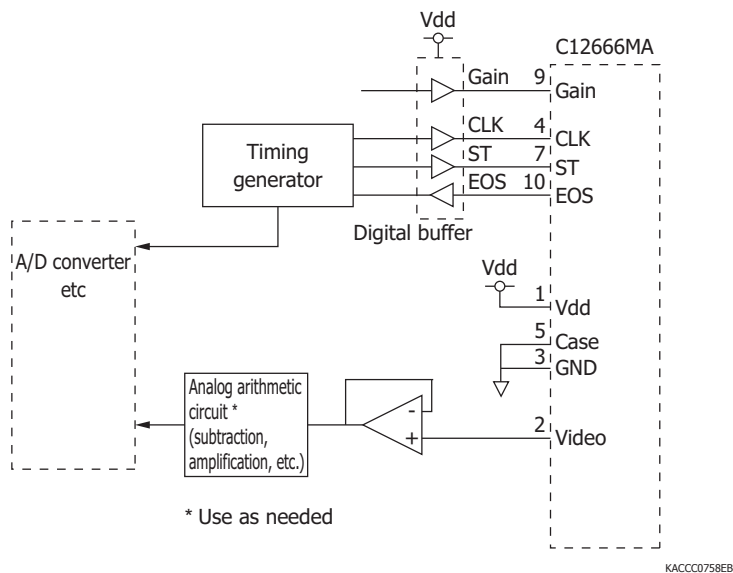
**Measurable incident light level**



\* Input spot diameter: 800 μm (λ=550 nm)

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**Recommended driver circuit example**

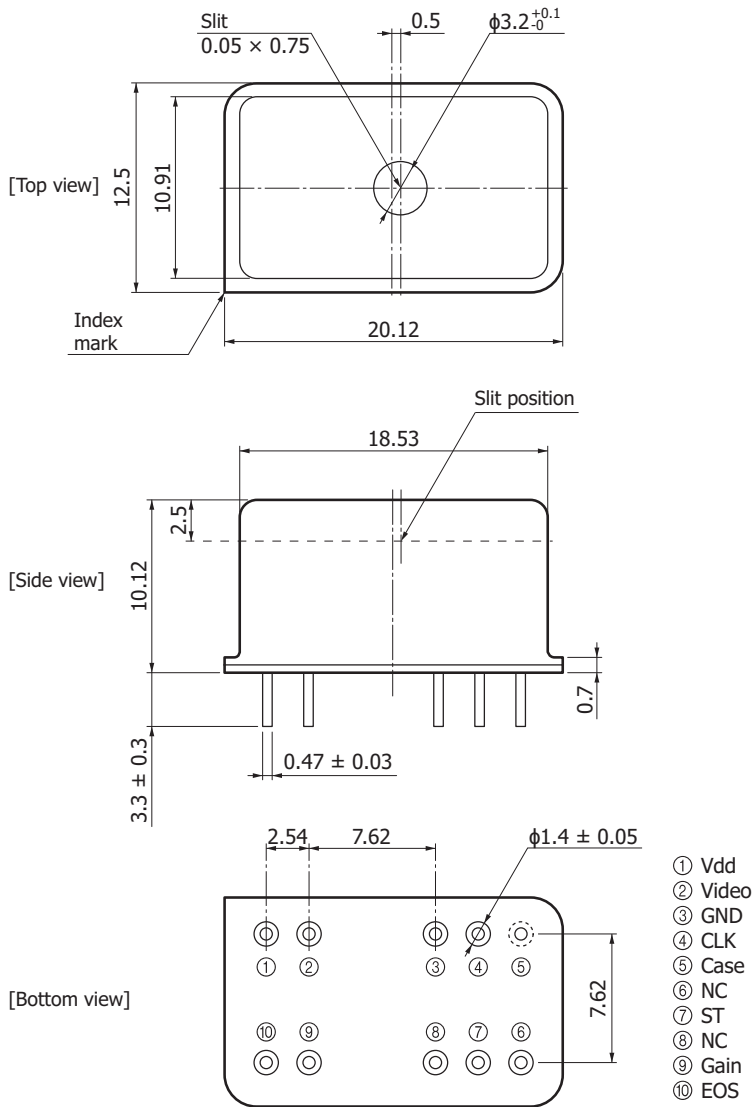


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**Precautions**

- The packaging of C12666MA is electrically conductive, so be careful when designing the circuit to avoid short circuit caused by contact with a circuit pattern.
- If external force is repeatedly applied to the lead pins, this may damage the lead pins.
- To prevent damage due to soldering, be careful of the soldering temperature and time.  
As a general guide, finish soldering within 3.5 seconds at 350 °C or less when soldering by hand, or within 10 seconds at 260 °C or less when using a solder bath.

**Dimensional outline (unit: mm, tolerance unless otherwise noted: ±0.2)**



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**Pin connections**

Make electrical connections to an external circuit using leads.

Pin no.	Symbol	Name	I/O	Description
1	Vdd	Supply voltage	I	Image sensor power supply: 5 V
2	Video	Video output	O	Video output signal
3	GND	Ground	-	Sensor ground
4	CLK	Clock pulse	I	Sensor scan sync signal
5	Case	Case	-	Case connection terminal
6	NC		-	No connection
7	ST	Start pulse	I	Start pulse
8	NC		-	No connection
9	Gain	Gain	I	Image sensor: Gain setting
10	EOS	End of scan	O	Sensor scan end signal

Note: Pin no. 9 is pulled up internally to Vdd via 10 kΩ.

Do not pull-up or pull-down the gain setting using an external circuit. For low gain, leave the pin open or connect to Vdd. For high gain, connect to GND.

## Internal CMOS image sensor specifications

### ▣ Recommended terminal voltage

Parameter	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	Vdd	4.75	5	5.25	V
Gain selection terminal voltage	High gain	0	-	0.4	V
	Low gain	Vdd - 0.25	Vdd	Vdd + 0.25	V
Clock pulse voltage	High level	Vdd - 0.25	Vdd	Vdd + 0.25	V
	Low level	0	-	0.4	V
Start pulse voltage	High level	Vdd - 0.25	Vdd	Vdd + 0.25	V
	Low level	0	-	0.4	V

### ▣ Electrical characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Clock pulse frequency*8	f(CLK)	1	-	800	kHz
Power consumption	High gain	-	-	60	mW
	Low gain	-	-	60	

\*8: Ta=25 °C, Vdd=5 V, V(CLK)=V(ST)=5

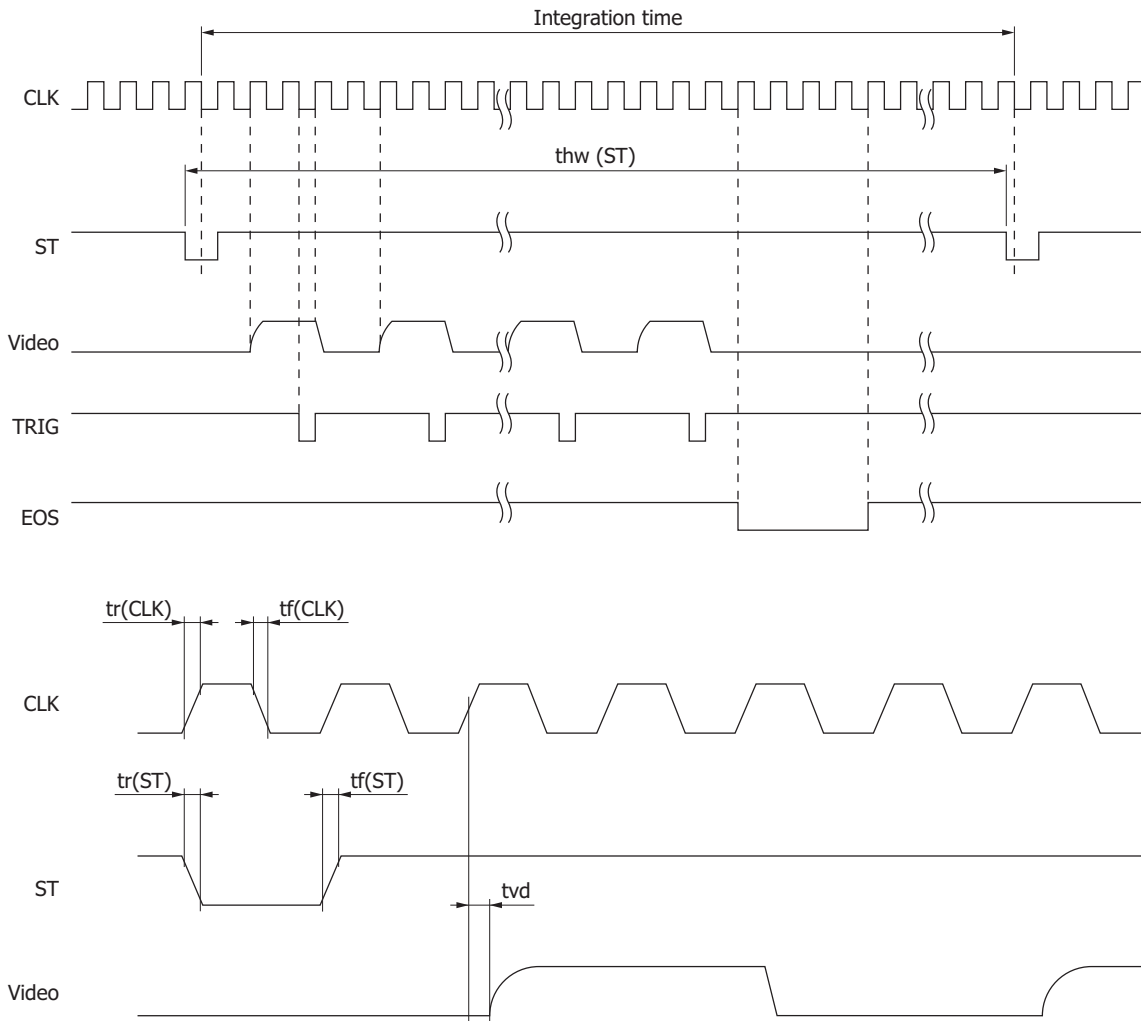
### ▣ Electrical and optical characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Dark current	High gain	-	0.02	0.08	pA
	Low gain	-	0.02	0.08	
Output offset voltage	High gain	0.15	0.35	0.55	V
	Low gain	0.15	0.35	0.55	
Charge amplifier feedback capacitance*9	High gain	-	1.4	-	pF
	Low gain	-	4.8	-	
Saturation output voltage*10	High gain	2.3	2.8	3.3	V
	Low gain	1.4	1.7	2.0	
Readout noise	High gain	-	0.3	0.5	mV rms
	Low gain	-	0.2	0.4	

\*9: Gain=5 V (low gain), Vg=0 V (high gain)

\*10: Voltage difference relative to Vo

**Timing chart**



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Parameter	Symbol	Min.	Typ.	Max.	Unit
Start pulse high period	thw(ST)	1030/f(CLK)	-	-	s
Start pulse rise/fall times	tr(ST), tf(ST)	0	20	30	ns
Clock pulse duty ratio	-	45	50	55	%
Clock pulse rise/fall times	tr(CLK), tf(CLK)	0	20	30	ns
Video delay time	tvd	-	20	-	ns

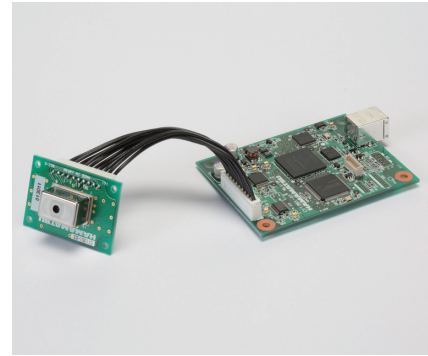
Note: The clock pulse should be set from high to low just once when the start pulse is low. The internal shift register starts operating at this timing.

The integration time is determined by the start pulse intervals. However, since the charge integration of each pixel is carried out between the signal readout of that pixel and the next signal readout of the same pixel, the start time of charge integration differs depending on each pixel. In addition, the next start pulse cannot be input until signal readout from all pixels is completed.

Video output is 1/4 of the clock pulse frequency.

### Micro-spectrometer evaluation circuit C11351-10 (sold separately)

The C11351-10 is a circuit board designed to simply evaluate the characteristics of the micro-spectrometer. The characteristics of the micro-spectrometer can be evaluated using the evaluation software by connecting the micro-spectrometer to a PC with a USB cable A9160 (AB type, sold separately)\*11.



#### Features

- Initial evaluation circuit for micro-spectrometer\*12
- Wavelength conversion factors of the micro-spectrometer can be input from a PC.\*13
- High A/D resolution (16-bit)
- USB powered

\*11: Compatible OS:

Microsoft® Windows® 7 Professional SP1 (32-bit), Microsoft® Windows® 7 Professional SP1 (64-bit)

Microsoft and Windows are registered trademarks of Microsoft Corporation in the United States and/or other countries.

\*12: The C11351-10 is a modified version of the C11351 evaluation circuit for the previous mini-spectrometer MS series (C10988MA-01, C11708MA). Only the sensor board has been modified. If you already have the C11351, you only have to purchase the C11351-03 (the sensor board for micro-spectrometers) to evaluate C12666MA micro-spectrometers.

\*13: A typical wavelength conversion factor is entered at the time of shipment of the C11351-10. To measure a spectrum with higher wavelength accuracy, it is necessary to input the wavelength conversion factor listed in the final inspection sheet that comes with each micro-spectrometer.

Note: Since the C11351-10 is an evaluation circuit for the micro-spectrometer, the DLL function specifications are not available to users.

#### Electrical characteristics

Parameter	Specification	Unit
Interface	USB 2.0	-
A/D conversion	16	bit
Clock pulse frequency	800	kHz
Video rate	200	kHz
Integration time	5 to 10000	ms

#### Structure

Parameter	Specification	Unit
Applicable spectrometer	C12666MA	-
Dimensions	Control board	80 × 60
	Sensor board	30 × 44

#### Absolute maximum ratings

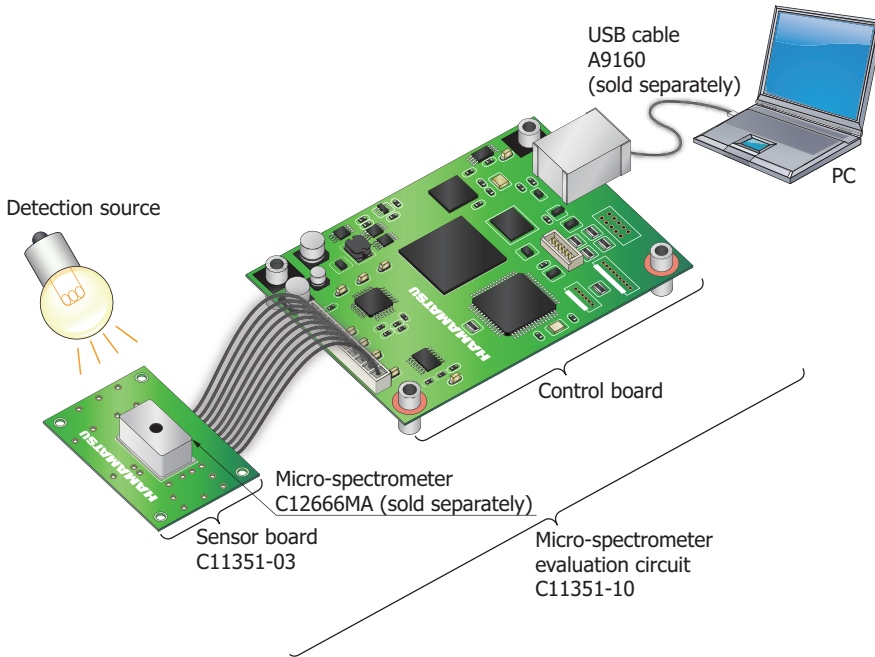
Parameter	Value	Unit
Operating temperature*14	+5 to +40	°C
Storage temperature*14	-20 to +70	°C

\*14: No condensation

Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

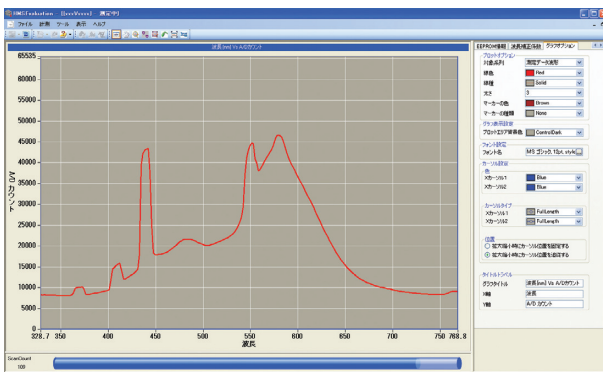


Connection example



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Evaluation software display example



Mini-spectrometer/micro-spectrometer lineup

Type no.	Type	Spectral response range (nm)														Spectral resolution max. (nm)	Image sensor		
		200	400	600	800	1000	1200	1400	1600	1800	2000	2200	2400	2600					
C10082CA	TM-UV/VIS-CCD High sensitivity																	6	Back-thinned CCD image sensor
C10082CAH	TM-UV/VIS-CCD High resolution		200 to 800															1*	
C10082MD	TM-UV/VIS-MOS Wide dynamic range																	6	CMOS linear image sensor
C10083CA	TM-VIS/NIR-CCD High sensitivity																	8 (λ=320 to 900 nm)	Back-thinned CCD image sensor
C10083CAH	TM-VIS/NIR-CCD High resolution																	1* (λ=320 to 900 nm)	
C10083MD	TM-VIS/NIR-MOS Wide dynamic range				320 to 1000													8	CMOS linear image sensor
C11697MB	TM-VIS/NIR-MOS-II Trigger-compatible																	8	High-sensitivity CMOS linear image sensor
C9404CA	TG-UV-CCD High sensitivity		200 to 400															3	Back-thinned CCD image sensor
C9404CAH	TG-UV-CCD High resolution																	1*	Back-thinned CCD image sensor
C9405CB	TG-SWNIR-CCD-II IR-enhanced				500 to 1100													5 (λ=550 to 900 nm)	IR-enhanced Back-thinned CCD image sensor
C11713CA	TG-RAMAN-I High resolution				500 to 600													0.3*	Back-thinned CCD image sensor
C11714CB	TG-RAMAN-II High resolution						790 to 920											0.3*	IR-enhanced Back-thinned CCD image sensor
C11482GA	TG2-NIR Non-cooled type								900 to 1700									7	InGaAs linear image sensor
C9913GC	TG-cooled NIR-I Low noise (cooled type)																	7	
C9914GB	TG-cooled NIR-II Low noise (cooled type)									1100 to 2200								8	
C11118GA	TG-cooled NIR-III Low noise (cooled type)										900 to 2550							20	
C13053MA	FT-SWIR-MOS-II Compact, thin				500 to 1100													3.5	High sensitivity CMOS linear image sensor
C11007MA	RC-VIS-MOS Spectrometer module		340 to 780															9	CMOS linear image sensor
C11008MA	RC-SWNIR-MOS Spectrometer module				640 to 1050													8	IR-enhanced CMOS linear image sensor

\* Typ.

For installation into mobile measuring equipment

Type no.	Type	Spectral response range (nm)														Spectral resolution max. (nm)	image sensor		
		200	400	600	800	1000	1200	1400	1600	1800	2000	2200	2400	2600					
C11009MA	RC-VIS-MOS Spectrometer head		340 to 780															9	CMOS linear image sensor
C11010MA	RC-SWNIR-MOS Spectrometer head				640 to 1050													8	IR-enhanced CMOS linear image sensor

For installation into mobile measuring equipment (ultra-compact type)

Type no.	Type	Spectral response range (nm)														Spectral resolution max. (nm)	image sensor		
		200	400	600	800	1000	1200	1400	1600	1800	2000	2200	2400	2600					
C10988MA-01	MS-VIS-MOS Spectrometer head		340 to 750															14	CMOS linear image sensor
C11708MA	MS-SWNIR-MOS Spectrometer head				640 to 1050													20	
C12666MA	Micro-spectrometer Spectrometer head		340 to 780															15	CMOS linear image sensor

## Related information

[www.hamamatsu.com/sp/ssd/doc\\_en.html](http://www.hamamatsu.com/sp/ssd/doc_en.html)

### ■ Precautions

- Notice

### ■ Technical information

- Mini-spectrometer / Technical information

Information described in this material is current as of December, 2014.

Product specifications are subject to change without prior notice due to improvements or other reasons. This document has been carefully prepared and the information contained is believed to be accurate. In rare cases, however, there may be inaccuracies such as text errors. Before using these products, always contact us for the delivery specification sheet to check the latest specifications.

The product warranty is valid for one year after delivery and is limited to product repair or replacement for defects discovered and reported to us within that one year period. However, even if within the warranty period we accept absolutely no liability for any loss caused by natural disasters or improper product use.

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